

Electronic Patent Application Fee Transmittal

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|---|---|-----------------|---------------|-----------------------------|
| Application Number: | 10689506 | | | |
| Filing Date: | 20-Oct-2003 | | | |
| Title of Invention: | High performance stress-enhanced MOSFETs using Si:C and SiGe epitaxial source/drain and method of manufacture | | | |
| First Named Inventor/Applicant Name: | Huajie Chen | | | |
| Filer: | Andrew Michael Calderon/Liping Qi | | | |
| Attorney Docket Number: | FIS920030241US1 | | | |
| Filed as Large Entity | | | | |
| Utility Filing Fees | | | | |
| Description | Fee Code | Quantity | Amount | Sub-Total in USD(\$) |
| Basic Filing: | | | | |
| Pages: | | | | |
| Claims: | | | | |
| Miscellaneous-Filing: | | | | |
| Petition: | | | | |
| Patent-Appeals-and-Interference: | | | | |
| Post-Allowance-and-Post-Issuance: | | | | |
| Extension-of-Time: | | | | |

| Description | Fee Code | Quantity | Amount | Sub-Total in USD(\$) |
|---|----------|----------|--------|----------------------|
| Miscellaneous: | | | | |
| Submission- Information Disclosure Stmt | 1806 | 1 | 180 | 180 |
| Total in USD (\$) | | | | 180 |